# DATA SHEET



# MOS FIELD EFFECT TRANSISTOR NP82N06PLG

## SWITCHING N-CHANNEL POWER MOS FET

## DESCRIPTION

The NP82N06PLG is N-channel MOS Field Effect Transistor designed for high current switching applications.

## ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP82N06PLG-E1-AY Note		Таре	
NP82N06PLG-E2-AY Note	Pure Sn (Tin)	800 p/reel	TO-263 (MP-25ZP)

Note Pb-free (This product does not contain Pb in the external electrode.)

## FEATURES

• Super low on-state resistance  $R_{DS(on)1}$  = 6.7 m $\Omega$  MAX. (VGs = 10 V, ID = 41 A)

- $R_{DS(on)2} = 8.5 \text{ m}\Omega \text{ MAX.} (V_{GS} = 5 \text{ V}, \text{ ID} = 41 \text{ A})$
- Low input capacitance
- Ciss = 5700 pF TYP.
- Built-in gate protection diode

## ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (VGs = 0 V)	VDSS	60	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	D(DC)	±82	Α
Drain Current (pulse) Note1	D(pulse)	±270	Α
Total Power Dissipation (Tc = 25°C)	P <sub>T1</sub>	143	W
Total Power Dissipation (T <sub>A</sub> = 25°C)	Рт2	1.8	W
Channel Temperature	Tch	175	°C
Storage Temperature	Tstg	-55 to +175	°C
Repetitive Avalanche Current Note2	AR	37	Α
Repetitive Avalanche Energy Note2	Ear	137	mJ

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

**2.** Tch ≤ 150°C, VDD = 30 V, RG = 25  $\Omega$ , VGS = 20  $\rightarrow$  0 V, L = 100  $\mu$ H

## THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	1.05	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W

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## ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
Gate Leakage Current	lgss	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Gate to Source Threshold Voltage Note	VGS(th)	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 41 A	19	40		S
Drain to Source On-state Resistance <sup>Note</sup>	RDS(on)1	Vgs = 10 V, Id = 41 A		5.1	6.7	mΩ
	RDS(on)2	Vgs = 5 V, Id = 41 A		6.4	8.5	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = 25 V,		5700	8550	pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V,		420	630	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		275	500	pF
Turn-on Delay Time	<b>t</b> d(on)	Vdd = 30 V, Id = 41 A,		28	70	ns
Rise Time	tr	V <sub>GS</sub> = 10 V,		22	60	ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 0 Ω		79	160	ns
Fall Time	tr			9	30	ns
Total Gate Charge	QG	V <sub>DD</sub> = 48 V,		106	160	nC
Gate to Source Charge	QGS	V <sub>GS</sub> = 10 V,		29		nC
Gate to Drain Charge	Qgd	ID = 82 A		35		nC
Body Diode Forward Voltage <sup>Note</sup>	VF(S-D)	IF = 82 A, VGS = 0 V		0.9	1.5	V
Reverse Recovery Time	trr	IF = 82 A, VGS = 0 V,		43		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ <i>µ</i> s		65		nC

Note Pulsed

#### TEST CIRCUIT 1 AVALANCHE CAPABILITY

#### **TEST CIRCUIT 2 SWITCHING TIME**



Starting Tch

#### **TEST CIRCUIT 3 GATE CHARGE**







GS lave Form	vgs 0 <u>10%-</u>	ļ	/ <sub>GS</sub>	90%
DS ave Form	VDS VDS 0 td(on)	tr ton	10% td(off)	90%

## TYPICAL CHARACTERISTICS (TA = 25°C)





FORWARD BIAS SAFE OPERATING AREA



#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



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GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



DRAIN TO SOURCE ON-STATE RESISTANCE vs.

 $R_{DS(on)}$  - Drain to Source On-state Resistance -  $m\Omega$ 

V<sub>GS(th)</sub> - Gate to Source Threshold Voltage - V



FORWARD TRANSFER CHARACTERISTICS

Ip - Drain Current - A



VGS - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT







 $R_{DS(on)}$  - Drain to Source On-state Resistance -  $m\Omega$ 

 $R_{DS(on)}$  - Drain to Source On-state Resistance -  $m\Omega$ 

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE







SOURCE TO DRAIN DIODE FORWARD VOLTAGE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE







REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



## PACKAGE DRAWING (Unit: mm)



## EQUIVALENT CIRCUIT



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

## TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



## MARKING INFORMATION



## **RECOMMENDED SOLDERING CONDITIONS**

The NP82N06PLG should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below	IR60-00-3
	Time at maximum temperature: 10 seconds or less	
	Time of temperature higher than 220°C: 60 seconds or less	
	Preheating time at 160 to 180°C: 60 to 120 seconds	
	Maximum number of reflow processes: 3 times	
	Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	
Partial heating	Maximum temperature (Pin temperature): 350°C or below	P350
	Time (per side of the device): 3 seconds or less	
	Maximum chlorine content of rosin flux: 0.2% (wt.) or less	

Caution Do not use different soldering methods together (except for partial heating).

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